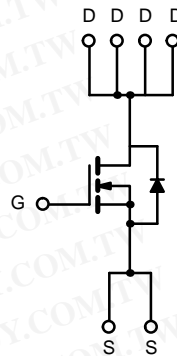
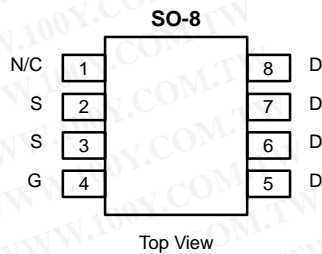




## N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
30	0.030 @ V <sub>GS</sub> = 10 V	7.0
	0.040 @ V <sub>GS</sub> = 5 V	6.0
	0.050 @ V <sub>GS</sub> = 4.5 V	5.4

勝特力材料 886-3-5753170  
 勝特力电子(上海) 86-21-54151736  
 勝特力电子(深圳) 86-755-83298787  
 Http://www.100y.com.tw



Ordering Information: Si9410DY  
 Si9410DY-T1 (with Tape and Reel)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		V <sub>GS</sub>	±20	
Continuous Drain Current (T <sub>J</sub> = 150°C) <sup>a</sup>	T <sub>A</sub> = 25°C	I <sub>D</sub>	7.0	A
	T <sub>A</sub> = 70°C		5.8	
Pulsed Drain Current		I <sub>DM</sub>	30	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	2.8	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25°C	P <sub>D</sub>	2.5	
	T <sub>A</sub> = 70°C		1.6	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	50	°C/W

Notes  
 a. Surface Mounted on FR4 Board, t ≤ 10 sec.  
 For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>


**SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.0			V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V			2	μA
		V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			25	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	30			A
Drain-Source On-State Resistance <sup>b</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.0 A		0.024	0.030	Ω
		V <sub>GS</sub> = 5 V, I <sub>D</sub> = 4.0 A		0.030	0.040	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3.5 A		0.032	0.050	
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 7.0 A		15		S
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>S</sub> = 2 A, V <sub>GS</sub> = 0 V		0.72	1.1	V
<b>Dynamic<sup>a</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7 A		24	50	nC
Gate-Source Charge	Q <sub>gs</sub>			2.8		
Gate-Drain Charge	Q <sub>gd</sub>			4.6		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 25 V, R <sub>L</sub> = 25 Ω I <sub>D</sub> ≅ 1 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 6 Ω		14	30	ns
Rise Time	t <sub>r</sub>			10	60	
Turn-Off Delay Time	t <sub>d(off)</sub>			46	150	
Fall Time	t <sub>f</sub>			17	140	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>		I <sub>F</sub> = 2 A, di/dt = 100 A/μs		60	

## Notes

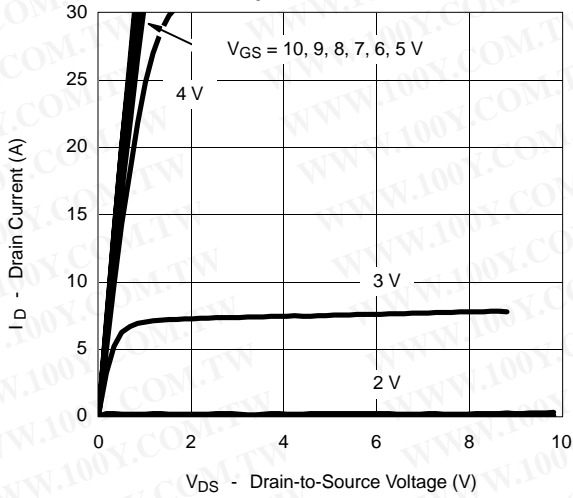
- a. Guaranteed by design, not subject to production testing.  
 b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

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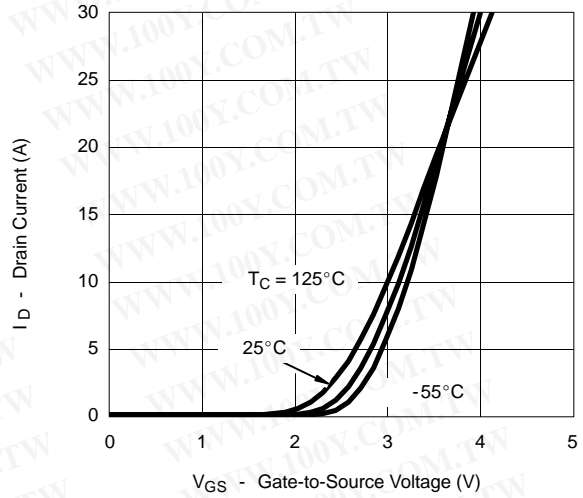


**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

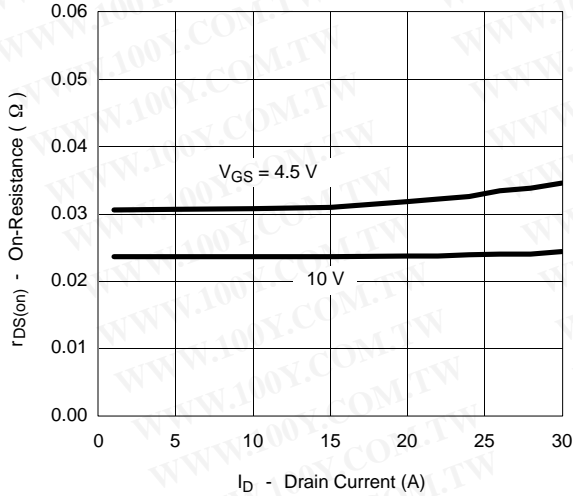
**Output Characteristics**



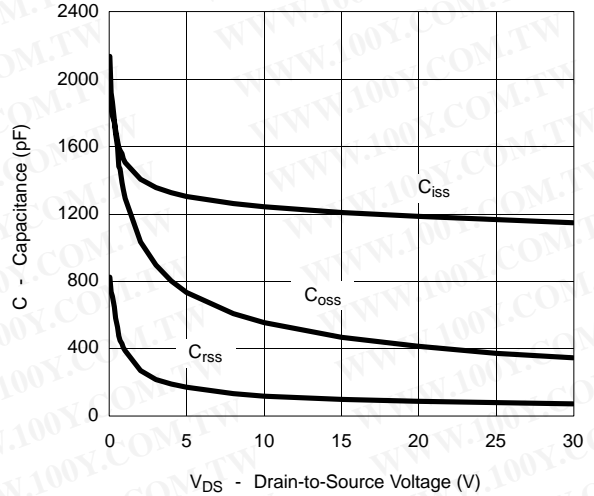
**Transfer Characteristics**



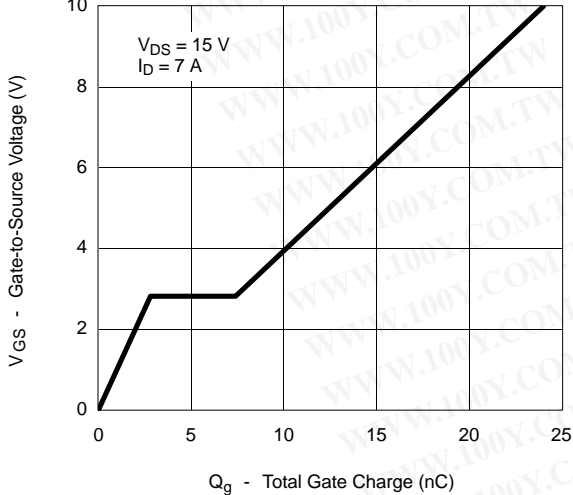
**On-Resistance vs. Drain Current**



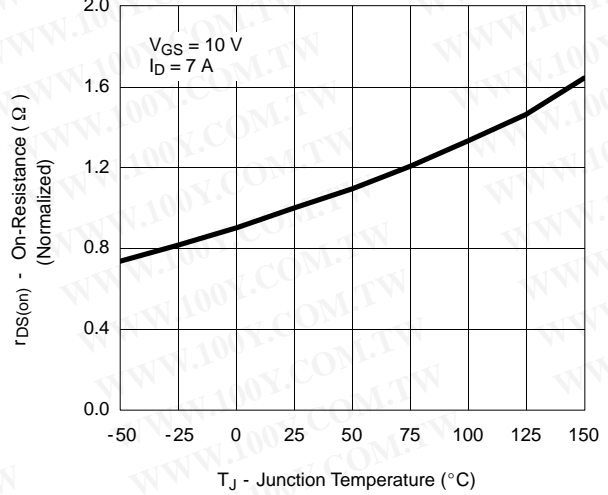
**Capacitance**



**Gate Charge**



**On-Resistance vs. Junction Temperature**





**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

